

40 V, 0.5 A PNP low VCEsat (BISS) transistor Rev. 1 — 7 March 2012

Product data sheet

1. **Product profile**

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS2540MB.

1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger

1.4 Quick reference data

- High efficiency due to less heat generation
- AEC-Q101 qualified
- Reduced Printed-Circuit Board (PCB) requirements
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-500	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-1	А
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	440	700	mΩ

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	E	emitter		3
3	С	collector	2	1
			Transparent top view	2
			SOT883B	sym013

3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
PBSS3540MB	-	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

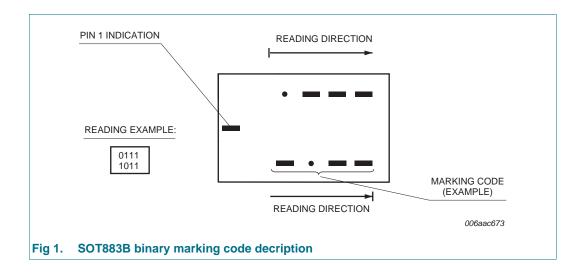
4. Marking

Table 4. Marking codes

•	
Type number	Marking code ^[1]
PBSS3540MB	0001 0100

[1] For SOT883B binary marking code description see Figure 1.

4.1 Binary marking code description



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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-40	V
V _{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1][2]</u>	-	250	mW
			[3][2]	-	590	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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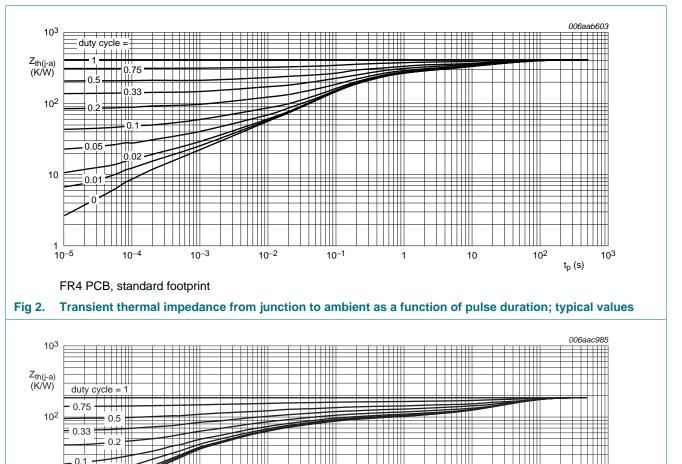
6. Thermal characteristics

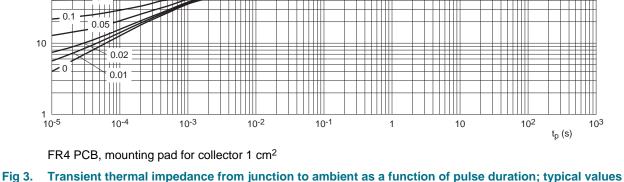
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1][2]</u>	-	-	500	K/W
	from junction to ambient		<u>[3][2]</u>	-	-	212	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommented soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².





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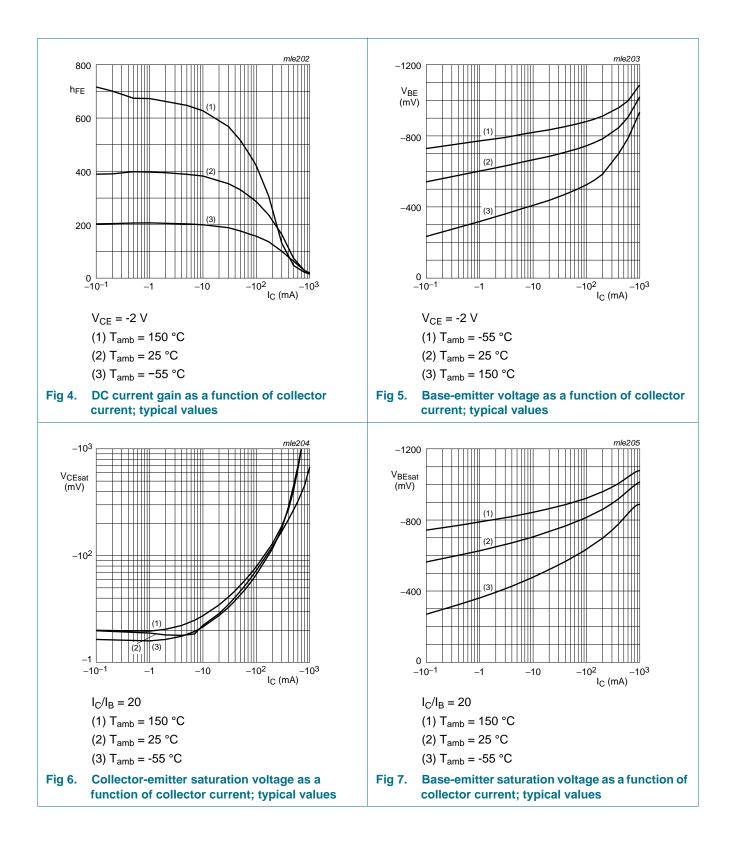
7. Characteristics

Cumber of	Devenueter	Conditions	N.4	True	Max	1 lm24
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -10 mA; T _{amb} = 25 °C	200	-	-	
			150	-	-	
			40	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -10 mA; I_{B} = -0.5 mA; T_{amb} = 25 °C	-	-	-50	mV
		$\begin{split} I_C &= -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^\circ\text{C} \end{split}$	-	-	-130	mV
		I_{C} = -200 mA; I_{B} = -10 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-200	mV
		I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-350	mV
R _{CEsat}	collector-emitter saturation resistance	$ I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{pulsed}; $	-	440	700	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$ \begin{array}{l} V_{CE} = -2 \ V; \ I_C = -100 \ mA; \ pulsed; \\ t_p \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array} $	-	-	-1.1	V
f _T	transition frequency	$\label{eq:Vce} \begin{array}{l} V_{CE} = -5 \ V; \ I_C = -100 \ mA; \ f = 100 \ MHz; \\ T_{amb} = 25 \ ^\circ C \end{array}$	100	300	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	10	pF

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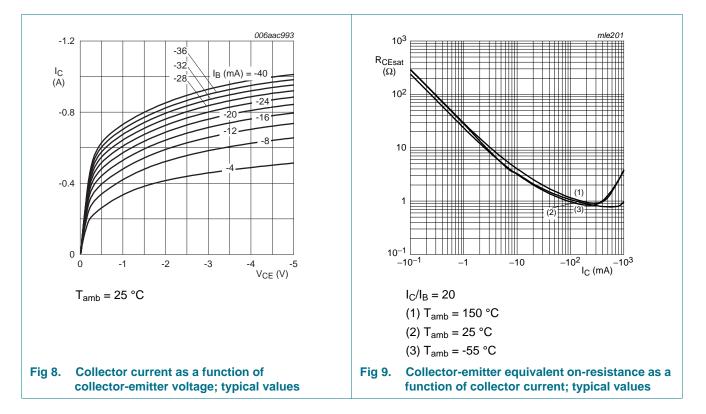
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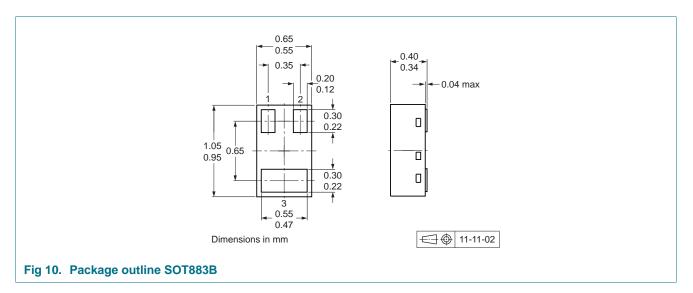
8. Test information

8.1 Quality information

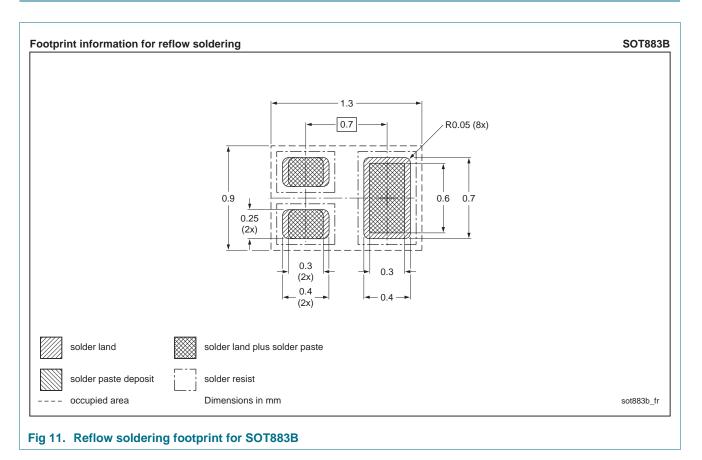
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline



10. Soldering



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11. Revision history

Table 8.	Revision history						
Document	ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS3540	MB v.1	20120307	Product data sheet	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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